Brian Bennett

List of Publications by Year
in descending order

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223 papers	9,493 citations	81900 39 h-index	43889 91 g-index
228 all docs	228 docs citations	228 times ranked	6002 citing authors

#	Article	IF	Citations
1	Charge scattering mechanisms in shallow InAs quantum wells. Journal of Applied Physics, 2020, 127, .	2.5	3
2	Effect of illumination on the interplay between Dresselhaus and Rashba spin-orbit couplings in InAs quantum wells. Journal of Applied Physics, 2019, 126, .	2.5	3
3	Single-Event Measurement and Analysis of Antimony-Based p-Channel Quantum-Well MOSFETs With High- $kappa $ Dielectric. IEEE Transactions on Nuclear Science, 2017, 64, 434-440.	2.0	1
4	Single event transient response of InGaSb p-MOSFETs using pulsed laser excitation: Comparison of buried-channel and surface-channel structures. , 2016, , .		1
5	Strained InGaSb/AlGa(As)Sb Quantum Wells for p-Channel Transistors. Journal of Electronic Materials, 2016, 45, 2757-2762.	2.2	0
6	Electronic properties of atomic-layer-deposited high-k dielectrics on GaSb(001) with hydrogen plasma pretreatment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 04E102.	1.2	6
7	Detection of ferromagnetic domain wall pinning and depinning with a semiconductor device. Journal of Applied Physics, 2015, 118, 234501.	2.5	0
8	Ultralow Resistance Ohmic Contacts for p-Channel InGaSb Field-Effect Transistors. IEEE Electron Device Letters, 2015, 36, 546-548.	3.9	14
9	Single Event Measurement and Analysis of Antimony Based n-Channel Quantum-Well MOSFET With High-<formula formulatype="inline"><tex Notation="TeX">$kappa$</tex> </formula> Dielectric. IEEE Transactions on Nuclear Science, 2015, 62, 2807-2814.	2.0	3
10	Growth and characterization of (110) InAs quantum well metamorphic heterostructures. Journal of Applied Physics, 2015, 117, .	2.5	1
11	Enhancing p-channel InGaSb QW-FETs via Process-Induced Compressive Uniaxial Strain. IEEE Electron Device Letters, 2014, 35, 1088-1090.	3.9	12
12	High quality HfO2/p-GaSb(001) metal-oxide-semiconductor capacitors with 0.8â€‰nm equivalent oxide thickness. Applied Physics Letters, 2014, 105, .	3.3	20
13	Ion-Induced Charge-Collection Transients in p-Channel AlGaSb/InGaSb Heterojunction Field-Effect Transistors. IEEE Transactions on Nuclear Science, 2014, 61, 1510-1515.	2.0	3
14	Step graded buffer for (110) InSb quantum wells grown by molecular beam epitaxy. Journal of Crystal Growth, 2014, 404, 122-129.	1.5	2
15	Strained InGaAs/InAlAs quantum wells for complementary IIIâ€“V transistors. Journal of Crystal Growth, 2014, 388, 92-97.	1.5	14
16	Integration of atomic layer deposited high-k dielectrics on GaSb via hydrogen plasma exposure. AIP Advances, 2014, 4, .	1.3	5
17	Effect of an in situ hydrogen plasma pre-treatment on the reduction of GaSb native oxides prior to atomic layer deposition. Applied Surface Science, 2013, 277, 167-175.	6.1	48
18	Antimonide-Based Heterostructure p-Channel MOSFETs With Ni-Alloy Source/Drain. IEEE Electron Device Letters, 2013, 34, 1367-1369.	3.9	29

#	Article	IF	Citations
19	Effect of Interface States on the Performance of Antimonide nMOSFETs. IEEE Electron Device Letters, 2013, 34, 360-362.	3.9	12
20	Enhanced hole mobility and density in GaSb quantum wells. Solid-State Electronics, 2013, 79, 274-280.	1.4	18
21	Effects of oxidant dosing on GaSb (100) prior to atomic layer deposition and high-performance antimonide-based P-channel MOSFETs with Ni-alloy S/D. , 2013, , .		2
22	Ion-induced charge-collection transients in p-channel AlGaSb/InGaSb field-effect transistors. , 2013, , .		0
23	III-Sb MOSFETS : Opportunities and Challenges. ECS Transactions, 2012, 45, 91-96.	0.5	2
24	Atomic layer deposition of Al2O3 on GaSb using in situ hydrogen plasma exposure. Applied Physics Letters, 2012, 101, 231601.	3.3	45
25	Amelioration of interface state response using band engineering in III-V quantum well metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2012, 100, .	3.3	9
26	InGaSb: Single channel solution for realizing III–V CMOS. , 2012, , .		10
27	Antimonide NMOSFET with source side injection velocity of 2.7×10⁷ cm/s for low power high performance logic applications. , 2012, , .		4
28	Enhancing hole mobility in III-V semiconductors. Journal of Applied Physics, 2012, 111, .	2.5	37
29	Heterostructure design and demonstration of InGaSb channel III-V CMOS transistors. , 2011, , .		4
30	Enhancement-Mode Antimonide Quantum-Well MOSFETs With High Electron Mobility and Gigahertz Small-Signal Switching Performance. IEEE Electron Device Letters, 2011, 32, 1689-1691.	3.9	21
31	Experimental determination of dominant scattering mechanisms in scaled InAsSb quantum well. , 2011, , .		2
32	Experimental Determination of Quantum and Centroid Capacitance in Arsenideâ€“Antimonide Quantum-Well MOSFETs Incorporating Nonparabolicity Effect. IEEE Transactions on Electron Devices, 2011, 58, 1397-1403.	3.0	18
33	Optimization of the $hbox{Al}_{2}hbox{O}_{3}/ hbox{GaSb}$ Interface and a High-Mobility GaSb pMOSFET. IEEE Transactions on Electron Devices, 2011, 58, 3407-3415.	3.0	89
34	Molecular Beam Epitaxial Regrowth of Antimonide-Based Semiconductors. Journal of Electronic Materials, 2011, 40, 6-10.	2.2	4
35	Study of Shubnikovâ€“de Haas oscillations and measurement of hole effective mass in compressively strained InXGa1â^'XSb quantum wells. Solid-State Electronics, 2011, 62, 138-141.	1.4	3
36	Fermi-level pinning at metal/antimonides interface and demonstration of antimonides-based metal S/D Schottky pMOSFETs. , 2011, , .		1

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37	Device quality Sb-based compound semiconductor surface: A comparative study of chemical cleaning. Journal of Applied Physics, 2011, 109, .	2.5	45
38	InxGa1-xSb channel p-metal-oxide-semiconductor field effect transistors: Effect of strain and heterostructure design. Journal of Applied Physics, 2011, 110, 014503.	2.5	37
39	Hole mobility enhancement in In0.41Ga0.59Sb quantum-well field-effect transistors. Applied Physics Letters, 2011, 98, 053505.	3.3	26
40	Open quantum dotsâ€"probing the quantum to classical transition. Semiconductor Science and Technology, 2011, 26, 043001.	2.0	44
41	AlGaSb Buffer Layers for Sb-Based Transistors. Journal of Electronic Materials, 2010, 39, 2196-2202.	2.2	7
42	Scaling projections for Sb-based p-channel FETs. Solid-State Electronics, 2010, 54, 1349-1358.	1.4	10
43	Advanced composite high-κ gate stack for mixed anion arsenide-antimonide quantum well transistors. , 2010, , .		7
44	Fermi level unpinning of GaSb(100) using Plasma Enhanced ALD Al<inf>2</inf>O<inf>3</inf> dielectric. , 2010, , .		5
45	Periodic Scarred States in Open Quantum Dots as Evidence of Quantum Darwinism. Physical Review Letters, 2010, 104, 176801.	7.8	44
46	Fermi level unpinning of GaSb (100) using plasma enhanced atomic layer deposition of Al2O3. Applied Physics Letters, 2010, 97, 143502.	3.3	97
47	Imaging periodic scarred states in InAs open quantum dots: Evidence of quantum darwinism. , 2010, , .		0
48	Development of high-k dielectric for antimonides and a sub 350°C III–V pMOSFET outperforming Germanium. , 2010, , .		31
49	Sb-based n- and p-channel HFETs for high-speed, low-power applications. , 2009, , .		2
50	Spatial localization of 1/f noise sources in AlSb/InAs high-electron-mobility transistors. Journal of Applied Physics, 2009, 106, .	2.5	2
51	Compound Semiconductors for Low-Power p-Channel Field-Effect Transistors. MRS Bulletin, 2009, 34, 530-536.	3.5	17
52	Demonstration of high-mobility electron and hole transport in a single InGaSb well for complementary circuits. Journal of Crystal Growth, 2009, 312, 37-40.	1.5	16
53	Engineering of strained III–V heterostructures for high hole mobility. , 2009, , .		13
54	Using Density-Gradient Theory to Model Sb-Based p-Channel FETs. , 2009, , .		1

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55	Manufacturable tri-stack AlSb/INAS HEMT low-noise amplifiers using wafer-level-packaging technology for light-weight and ultralow-power applications. , 2009, , .		0
56	Imaging scarred states in quantum dots. Journal of Physics Condensed Matter, 2009, 21, 212201.	1.8	8
57	Strained GaSb/AlAsSb quantum wells for p-channel field-effect transistors. Journal of Crystal Growth, 2008, 311, 47-53.	1.5	55
58	1/f noise of Sb-based p-channel HFETs. Electronics Letters, 2008, 44, 1155.	1.0	1
59	Antimonide-based diodes for terahertz mixers. Applied Physics Letters, 2008, 92, .	3.3	7
60	The effect of gate metals on manufacturability of 0.1 μm metamorphic AlSb/InAs HEMTs for ultralow-power applications. , 2008, , .		3
61	Sb-Based n- and p-Channel Heterostructure FETs for High-Speed, Low-Power Applications. IEICE Transactions on Electronics, 2008, E91-C, 1050-1057.	0.6	28
62	High mobility p-channel HFETs using strained Sb-based materials. Electronics Letters, 2007, 43, 834.	1.0	37
63	Reliability Evaluation of 0.1 Â¿m AlSb/InAs HEMT Low Noise Amplifiers for Ultralow-Power Applications. , 2007, , .		6
64	Mobility enhancement in strained p-InGaSb quantum wells. Applied Physics Letters, 2007, 91, .	3.3	93
65	Manufacturable and Reliable 0.1 μm AlSb/InAs HEMT MMIC Technology for Ultra-Low Power Applications. , 2007, , .		12
66	0.1 μm In₀₂Al₀₈Sb-InAs HEMT low-noise amplifiers for ultralow-power applications. , 2007, , .		0
67	0.1 um n+-InAs-AlSb-InAs HEMT MMIC Technology for Phased-Array Applications. , 2007, , .		1
68	Growth of dilute nitride alloys of GaInSb lattice-matched to GaSb. Journal of Crystal Growth, 2007, 304, 338-341.	1.5	8
69	Low-Frequency Noise in AlSb/InAs and Related HEMTs. IEEE Transactions on Electron Devices, 2007, 54, 1193-1202.	3.0	26
70	InAlSb/InAs/AlGaSb Quantum Well Heterostructures for High-Electron-Mobility Transistors. Journal of Electronic Materials, 2007, 36, 99-104.	2.2	15
71	A Low Power/Low Noise MMIC Amplifier for Phased-Array Applications using InAs/AlSb HEMT. , 2006, , .		20
72	Pd/Pt/Au ohmic contact for AlSb/InAs0.7Sb0.3 heterostructures. Solid-State Electronics, 2006, 50, 429-432.	1.4	6

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73	InAsâˆ•AlSb high-electron-mobility transistors by molecular-beam epitaxy for low-power applications. Journal of Vacuum Science & Technology B, 2006, 24, 2581.	1.3	10
74	InAs HEMT narrowband amplifier with ultra-low power dissipation. Electronics Letters, 2006, 42, 688.	1.0	21
75	Band anticrossing in GaNxSb1â^'x. Applied Physics Letters, 2006, 89, 111921.	3.3	55
76	W-structured type-II superlattice-based long- and very long wavelength infrared photodiodes. , 2005, , .		26
77	Growth of InP high electron mobility transistor structures with Te doping. Journal of Crystal Growth, 2005, 278, 596-599.	1.5	2
78	Growth of dilute GaNSb by plasma-assisted MBE. Journal of Crystal Growth, 2005, 278, 188-192.	1.5	31
79	Antimonide-based compound semiconductors for electronic devices: A review. Solid-State Electronics, 2005, 49, 1875-1895.	1.4	319
80	InAlAsSbâˆ•InGaSb double heterojunction bipolar transistor. Electronics Letters, 2005, 41, 370.	1.0	11
81	Sb-based HEMTs with InAlSbâˆ•InAs heterojunction. Electronics Letters, 2005, 41, 1088.	1.0	18
82	Growth of InAsSb-channel high electron mobility transistor structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1441.	1.6	26
83	Shallow and thermally stable Ptâˆ•Wâˆ•Au Ohmic contacts to p-type InGaSb. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 293-297.	2.1	8
84	Band gap reduction in GaNSb alloys due to the anion mismatch. Applied Physics Letters, 2005, 87, 132101.	3.3	49
85	High radiation tolerance of InAsâˆ•AlSb high-electron-mobility transistors. Applied Physics Letters, 2005, 87, 173501.	3.3	30
86	A W-band InAs/AlSb low-noise/low-power amplifier. IEEE Microwave and Wireless Components Letters, 2005, 15, 208-210.	3.2	50
87	Materials growth for InAs high electron mobility transistors and circuits. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 688.	1.6	29
88	Low-frequency noise in AlSbâˆ•InAs high-electron-mobility transistor structure as a function of temperature and illumination. Applied Physics Letters, 2004, 85, 774-776.	3.3	16
89	Characterization of single magnetic particles with InAs quantum-well Hall devices. Applied Physics Letters, 2004, 85, 4693-4695.	3.3	25
90	Low-frequency noise characteristics of AlSb/InAsSb HEMTs. Solid-State Electronics, 2004, 48, 2079-2084.	1.4	13

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91	Arsenic cross-contamination in GaSb/InAs superlattices. Journal of Crystal Growth, 2004, 270, 301-308.	1.5	14
92	Sulfur passivation for shallow Pdâ•Wâ•Au ohmic contacts to p-InGaSb. Applied Physics Letters, 2004, 85, 3471-3473.	3.3	10
93	Transient response of III-V field-effect transistors to heavy-ion irradiation. IEEE Transactions on Nuclear Science, 2004, 51, 3324-3331.	2.0	26
94	X-ray diffraction analysis of lateral composition modulation in InAs/GaSb superlattices intended for infrared detector applications. IEE Proceedings: Optoelectronics, 2003, 150, 420.	0.8	0
95	AlSb/InAs HEMTs with a TiW/Au gate metalization for improved stability. Solid-State Electronics, 2003, 47, 181-184.	1.4	8
96	Controlled n-type doping of antimonides and arsenides using GaTe. Journal of Crystal Growth, 2003, 251, 532-537.	1.5	12
97	Very-long wave ternary antimonide superlattice photodiode with 21 Î¼m cutoff. Applied Physics Letters, 2003, 82, 4411-4413.	3.3	39
98	Lateral composition modulation in InAs/GaSb superlattices. Journal of Applied Physics, 2003, 93, 311-315.	2.5	13
99	Magnetotunneling between two-dimensional electron gases in InAs-AlSb-GaSb heterostructures. Physical Review B, 2003, 68, .	3.2	1
100	Modeling gate leakage in InAs/AlSb HEMTs. , 2003, , .		0
101	Design of a shallow thermally stable ohmic contact to p-type InGaSb. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 633.	1.6	21
102	Spontaneous growth of an InAs nanowire lattice in an InAs/GaSb superlattice. Applied Physics Letters, 2002, 81, 4452-4454.	3.3	21
103	Suppression of Bulk Defects in Antimonide Superlattice Infrared Photodiodes. Materials Research Society Symposia Proceedings, 2002, 722, 1011.	0.1	6
104	Characterization of InGaSb by photoreflectance spectroscopy. Journal of Applied Physics, 2002, 91, 1175-1178.	2.5	6
105	Heterostructure interface effects on the far-infrared magneto-optical spectra of InAs/Gasb quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 186-189.	2.7	5
106	Surface morphology of homoepitaxial GaSb films grown on flat and vicinal substrates. Journal of Crystal Growth, 2002, 236, 155-164.	1.5	36
107	Initial stages of Sb2 deposition on InAs(001). Surface Science, 2001, 478, 1-8.	1.9	6
108	Barrier roughness effects in resonant interband tunnel diodes. Journal of Applied Physics, 2001, 90, 6177-6181.	2.5	13

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109	Proton irradiation of InAs/AlSb/GaSb resonant interband tunneling diodes. Applied Physics Letters, 2001, 78, 2581-2583.	3.3	9
110	Charge-collection dynamics of AlSb-InAs-GaSb resonant interband tunneling diodes (RITDs) [for MOBILE logic circuits]. IEEE Transactions on Nuclear Science, 2001, 48, 1973-1979.	2.0	8
111	Effects of As[sub 2] versus As[sub 4] on InAs/GaSb heterostructures: As-for-Sb exchange and film stability. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1626.	1.6	38
112	Resonant interband tunnel diodes with AlGaSb barriers. Journal of Applied Physics, 2001, 89, 5791-5793.	2.5	9
113	Stoichiometry-induced roughness on antimonide growth surfaces. Applied Physics Letters, 2001, 78, 2440-2442.	3.3	8
114	Surface reconstruction phase diagrams for InAs, AlSb, and GaSb. Journal of Crystal Growth, 2000, 220, 384-392.	1.5	131
115	Magnetoelectronic latching Boolean gate. Solid-State Electronics, 2000, 44, 1099-1104.	1.4	27
116	Monolithic integration of resonant interband tunneling diodes and high electron mobility transistors in the InAs/GaSb/AlSb material system. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 1650.	1.6	21
117	Low-frequency noise in AlSb/InAs HEMTs. Electronics Letters, 2000, 36, 1888.	1.0	12
118	Observation of spin polarized transport across a ferromagnetâ€“two-dimensional electron gas interface (invited). Journal of Applied Physics, 2000, 87, 4665-4669.	2.5	24
119	Transport properties of Be- and Si-doped AlSb. Journal of Applied Physics, 2000, 87, 7876-7879.	2.5	16
120	Hammaret al.Reply:. Physical Review Letters, 2000, 84, 5024-5025.	7.8	52
121	Photoluminescence of InAs1â^'xSbx/AlSb single quantum wells: Transition from type-II to type-I band alignment. Journal of Applied Physics, 2000, 87, 8192-8194.	2.5	15
122	Interpreting interfacial structure in cross-sectional STM images of IIIâ€“V semiconductor heterostructures. Surface Science, 2000, 465, 361-371.	1.9	39
123	Deep level transient capacitance measurements of GaSb self-assembled quantum dots. Journal of Applied Physics, 2000, 88, 5843-5849.	2.5	35
124	Robust electrical spin injection into a semiconductor heterostructure. Physical Review B, 2000, 62, 8180-8183.	3.2	466
125	Electrical spin injection across air-exposed epitaxially regrown semiconductor interfaces. Applied Physics Letters, 2000, 77, 3989-3991.	3.3	60
126	Charge-collection characteristics of low-power ultrahigh speed, metamorphic AlSb/InAs high-electron mobility transistors (HEMTs). IEEE Transactions on Nuclear Science, 2000, 47, 2662-2668.	2.0	24

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127	Low-voltage, high-speed AlSb/InAsSb HEMTs. Electronics Letters, 1999, 35, 847.	1.0	24
128	Characterization of AlSb/InAs surfaces and resonant tunneling devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1786.	1.6	19
129	Engineered heterostructures of 6.1-Angstrom III-V semiconductors for advanced electronic and optoelectronic applications. , 1999, 3790, 13.		13
130	Observation of Spin Injection at a Ferromagnet-Semiconductor Interface. Physical Review Letters, 1999, 83, 203-206.	7.8	445
131	Anion control in molecular beam epitaxy of mixed As/Sb III-V heterostructures. Journal of Applied Physics, 1999, 85, 2157-2161.	2.5	38
132	Strong emission from As monolayers in AlSb. Physical Review B, 1999, 59, 2240-2244.	3.2	12
133	Optimum growth parameters for type-II infrared lasers. Journal of Applied Physics, 1999, 86, 1796-1799.	2.5	37
134	Optical and magnetic resonance studies of As-impurities in AlSb: from isoelectronic point defects to planes. Physica B: Condensed Matter, 1999, 273-274, 811-814.	2.7	1
135	Effects of surface reconstruction on IIIâ€“V semiconductor interface formation: The role of III/V composition. Applied Physics Letters, 1999, 74, 1704-1706.	3.3	38
136	Determination of temperature dependence of GaSb absorption edge and its application for transmission thermometry. Journal of Applied Physics, 1999, 85, 6632-6635.	2.5	21
137	Ohmic contacts in AlSb/InAs high electron mobility transistors for low-voltage operation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1022.	1.6	39
138	The structure of Sb-terminated GaAs(001) surfaces. Surface Science, 1999, 436, L707-L714.	1.9	34
139	Magnetocapacitance and far-infrared photoconductivity in GaSb/InAs composite quantum wells. Physical Review B, 1999, 60, R13958-R13961.	3.2	11
140	Molecular Beam Epitaxy of Sb-based Semiconductors. Series on Directions in Condensed Matter Physics, 1999, , 401-452.	0.1	7
141	Morphological instability in InAs/GaSb heterostructures. Journal of Crystal Growth, 1998, 191, 651-662.	1.5	7
142	AlSb/InAs HEMT's for low-voltage, high-speed applications. IEEE Transactions on Electron Devices, 1998, 45, 1869-1875.	3.0	124
143	Growth and characterisation of InAs/InGaSb/InAs/AlSb infrared laser structures. Electronics Letters, 1998, 34, 270.	1.0	45
144	Strain relaxation in InAs/GaSb heterostructures. Applied Physics Letters, 1998, 73, 3736-3738.	3.3	25

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145	Hybrid ferromagnet-semiconductor nonvolatile gate. IEEE Transactions on Magnetics, 1998, 34, 1054-1059.	2.1	17
146	Interfacial disorder in InAs/GaSb superlattices. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 7-30.	0.6	20
147	AlSb/InAs HEMTs using modulation InAs(Si)-doping. Electronics Letters, 1998, 34, 403.	1.0	12
148	0.1 [micro sign]m AlSb/InAs HEMTs with InAs subchannel. Electronics Letters, 1998, 34, 1525.	1.0	35
149	Auger coefficients in type-II InAs/Ga1â^'xInxSb quantum wells. Applied Physics Letters, 1998, 73, 2857-2859.	3.3	128
150	Modulation doping of InAs/AlSb quantum wells using remote InAs donor layers. Applied Physics Letters, 1998, 72, 1193-1195.	3.3	34
151	Nanometer scale surface clustering on ZnSe epilayers. Applied Physics Letters, 1998, 72, 1238-1240.	3.3	45
152	Above-room-temperature optically pumped midinfrared W lasers. Applied Physics Letters, 1998, 73, 3833-3835.	3.3	76
153	Structure of InAs/AlSb/InAs resonant tunneling diode interfaces. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2381.	1.6	19
154	Nanostructure patterns written in IIIâ€“V semiconductors by an atomic force microscope. Applied Physics Letters, 1997, 70, 1855-1857.	3.3	92
155	Synthetic wide bandpass x-ray polarizers. Applied Physics Letters, 1997, 70, 2224-2226.	3.3	1
156	Metallic III-V (001) Surfaces: Violations of the Electron Counting Model. Physical Review Letters, 1997, 79, 693-696.	7.8	76
157	A tunneling field-effect transistor with 25 nm metallurgical channel length. Applied Physics Letters, 1997, 70, 3005-3007.	3.3	12
158	The Growth of Type-II Infrared Laser Structures. Materials Research Society Symposia Proceedings, 1997, 484, 11.	0.1	0
159	Microwave noise characteristics of AlSb/InAs HEMTs. Electronics Letters, 1997, 33, 1092.	1.0	9
160	Evidence of a Hybridization Gap in ``Semimetallic'' InAs/GaSb Systems. Physical Review Letters, 1997, 78, 4613-4616.	7.8	158
161	Hybrid Hall effect device. Applied Physics Letters, 1997, 71, 974-976.	3.3	186
162	A RHEED and STM study of Sb-rich AlSb and GaSb (0 0 1) surface reconstructions. Journal of Crystal Growth, 1997, 175-176, 317-322.	1.5	27

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163	Composition and strain of self-assembled (In,Ga,Al)Sb/(Ga,Al)As quantum dots. Superlattices and Microstructures, 1997, 21, 267-272.	3.1	15
164	Stranski-Krastanov growth of InSb, GaSb, and AlSb on GaAs: structure of the wetting layers. Journal of Crystal Growth, 1997, 175-176, 888-893.	1.5	40
165	Molecular beam epitaxial growth of InSb, GaSb, and AlSb nanometerâ€scale dots on GaAs. Applied Physics Letters, 1996, 68, 505-507.	3.3	129
166	Photoluminescence studies of selfâ€assembled InSb, GaSb, and AlSb quantum dot heterostructures. Applied Physics Letters, 1996, 68, 3614-3616.	3.3	148
167	Phonons in selfâ€assembled (In,Ga,Al)Sb quantum dots. Applied Physics Letters, 1996, 68, 958-960.	3.3	56
168	A composite quantum well fieldâ€effect transistor. Applied Physics Letters, 1996, 69, 85-87.	3.3	19
169	Evolution of GaSb epitaxy on GaAs(001)â€c(4Ã—4). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 885-889.	2.1	40
170	AlSb/InAs HEMTs with high transconductance and negligible kink effect. Electronics Letters, 1996, 32, 688.	1.0	9
171	Characterization of surface roughness anisotropy on mismatched InAlAs/InP heterostructures. Journal of Electronic Materials, 1996, 25, 313-319.	2.2	6
172	Nucleation and growth of Fe on GaAs(001)-(2Ã—4) studied by scanning tunneling microscopy. Physical Review B, 1996, 53, R10481-R10484.	3.2	56
173	Observation of electrically resettable negative persistent photoconductivity in InAs/AlSb single quantum wells. Applied Physics Letters, 1996, 69, 1417-1419.	3.3	27
174	Self-assembled InSb and GaSb quantum dots on GaAs(001). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 2195.	1.6	41
175	Charge trapping and built-in field studies in electroreflectance of a GaAs structure. Semiconductor Science and Technology, 1996, 11, 521-524.	2.0	5
176	Epitaxial growth, structure, and composition of Fe films on GaAs(001)-2Ã—4. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 3193.	1.6	40
177	<title>InAs-GaSb-AlSb quantum confined structures for IR applications</title>. , 1995, , .		1
178	Surface photovoltage spectroscopy of InxAl1â^'xAs epilayers. Journal of Applied Physics, 1995, 78, 7163-7169.	2.5	8
179	Influence of interace and buffer layer on the structure of InAs/GaSb superlattices. Applied Physics Letters, 1995, 67, 1609-1611.	3.3	12
180	Origins of interfacial disorder in GaSb/InAs superlattices. Applied Physics Letters, 1995, 67, 3578-3580.	3.3	25

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181	0.2 Âµm AlSb/InAs HEMTs with 5 V gate breakdown voltage. Electronics Letters, 1994, 30, 1983-1984.	1.0	5
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